/ Revised record

F	2017-4				
G	2019-11-11	2	V_{CBO} V_{CEO} V_{EBO} I_{CEO}		
H	2020-5-21	1			
A	2022-2-9	all	BR Q AEC-Q101 , H Q 245±5℃ 5±0.5sec 255±5℃ 5±0.5sec		

SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

, BRMMBT5551Q AEC-Q101
High voltage, c

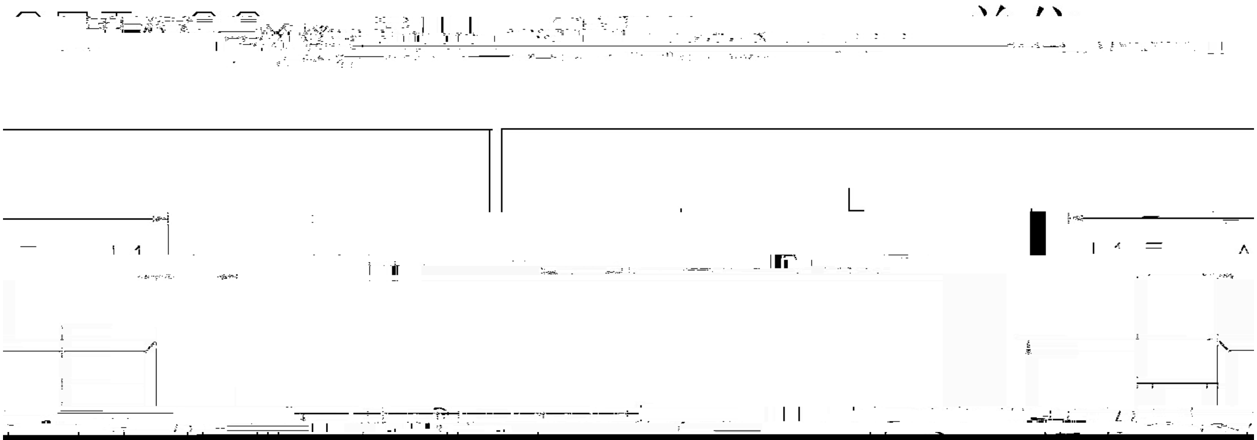
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-180	V
Collector to Emitter Voltage	V_{CEO}	-160	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current	I_C	-600	mA
Base Current	I_B	-300	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	[redacted]	[redacted]

[redacted]

Parameter	Symbol	Test Conditions	[redacted]

/ Electrical Characteristic Curve

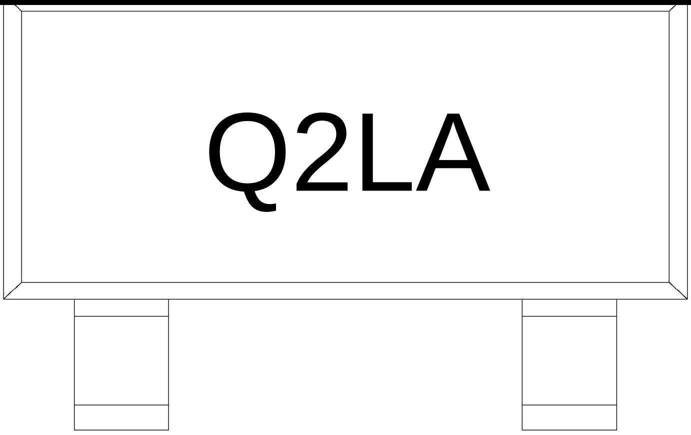
/ Package Dimensions



[redacted]

/ Marking Instructions

[redacted]



Q

2L

A h_{FE}

Note:

Q:	Automobile halogen-free product Code
2L	Product Type Code
A	h_{FE} Classifications Symbol Code

(   ) / Temperature Profile for IR Reflow Soldering(Pb-Free)

		Note:
1	150 200 60 120sec;	1.Preheating:150~200℃, Time:60~120sec.
2	255±5 5±0.5sec;	2.Peak Temp.:255±5℃, Duration:5±0.5sec.
3	2 10℃/sec.	3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

260±5℃ 10±1 sec. Temp.:260±5 Time:10±1 sec